



**SEMITRANS<sup>®</sup> 2**

## IGBT Modules

**SKM 145GB123D**

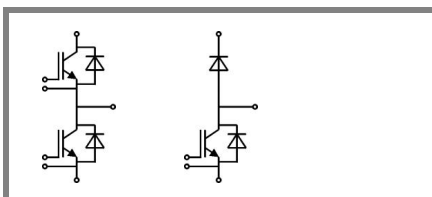
**SKM 145GAL123D**

### Features

- MOS input (voltage controlled)
- N channel, Homogeneous Si
- Low inductance case
- Very low tail current with low temperature dependence
- High short circuit capability, self limiting to  $6 \times I_{Cnom}$
- Latch-up free
- Fast & soft inverse CAL diodes
- Isolated copper baseplate using DCB Direct Copper Bonding
- Large clearance (10 mm) and creepage distances (20 mm)

### Typical Applications\*

- Switching (not for linear use)
- AC inverter drives



**GB**

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Absolute Maximum Ratings		$T_C = 25\text{ }^\circ\text{C}$ , unless otherwise specified			
Symbol	Conditions	Values		Units	
<b>IGBT</b>					
$V_{CES}$	$T_j = 25\text{ }^\circ\text{C}$	1200		V	
$I_C$	$T_j = 150\text{ }^\circ\text{C}$	$T_{case} = 25\text{ }^\circ\text{C}$	145	A	
		$T_{case} = 80\text{ }^\circ\text{C}$	110	A	
$I_{CRM}$	$I_{CRM} = 2 \times I_{Cnom}$	200		A	
$V_{GES}$		$\pm 20$		V	
$t_{psc}$	$V_{CC} = 600\text{ V}; V_{GE} \leq 20\text{ V}; T_j = 125\text{ }^\circ\text{C}$ $V_{CES} < 1200\text{ V}$	10		$\mu\text{s}$	
<b>Inverse Diode</b>					
$I_F$	$T_j = 150\text{ }^\circ\text{C}$	$T_{case} = 25\text{ }^\circ\text{C}$	130	A	
		$T_{case} = 80\text{ }^\circ\text{C}$	90	A	
$I_{FRM}$	$I_{FRM} = 2 \times I_{Fnom}$	200		A	
$I_{FSM}$	$t_p = 10\text{ ms}; \sin.$	$T_j = 150\text{ }^\circ\text{C}$	900		A
<b>Freewheeling Diode</b>					
$I_F$	$T_j = 150\text{ }^\circ\text{C}$	$T_{case} = 25\text{ }^\circ\text{C}$	170	A	
		$T_{case} = 80\text{ }^\circ\text{C}$	115	A	
$I_{FRM}$	$I_{FRM} = 2 \times I_{Fnom}$	300		A	
$I_{FSM}$	$t_p = 10\text{ ms}; \sin.$	$T_j = 150\text{ }^\circ\text{C}$	1440		A
<b>Module</b>					
$I_{t(RMS)}$		200		A	
$T_{vj}$		- 40 ... + 150		$^\circ\text{C}$	
$T_{stg}$		- 40 ... + 125		$^\circ\text{C}$	
$V_{isol}$	AC, 1 min.	2500		V	

Characteristics		$T_C = 25\text{ }^\circ\text{C}$ , unless otherwise specified				
Symbol	Conditions	min.	typ.	max.	Units	
<b>IGBT</b>						
$V_{GE(th)}$	$V_{GE} = V_{CE}, I_C = 4\text{ mA}$	4,5	5,5	6,5	V	
$I_{CES}$	$V_{GE} = 0\text{ V}, V_{CE} = V_{CES}$	$T_j = 25\text{ }^\circ\text{C}$		0,1	0,3	mA
$V_{CE0}$		$T_j = 25\text{ }^\circ\text{C}$		1,4	1,6	V
		$T_j = 125\text{ }^\circ\text{C}$		1,6	1,8	V
$r_{CE}$	$V_{GE} = 15\text{ V}$	$T_j = 25\text{ }^\circ\text{C}$		11	14	$\text{m}\Omega$
		$T_j = 125\text{ }^\circ\text{C}$		15	19	$\text{m}\Omega$
$V_{CE(sat)}$	$I_{Cnom} = 100\text{ A}, V_{GE} = 15\text{ V}$	$T_j = \text{ }^\circ\text{C}_{chiplev.}$		2,5	3	V
$C_{ies}$	$V_{CE} = 25, V_{GE} = 0\text{ V}$	$f = 1\text{ MHz}$		6,5	8,5	nF
$C_{oes}$				1	1,5	nF
$C_{res}$				0,5	0,6	nF
$Q_G$	$V_{GE} = -8\text{ V} - +20\text{ V}$			1000	nC	
$R_{Gint}$	$T_j = \text{ }^\circ\text{C}$			5	$\Omega$	
$t_{d(on)}$	$R_{Gon} = 6,8\ \Omega$	$V_{CC} = 600\text{ V}$ $I_C = 100\text{ A}$	160	320	ns	
$t_r$			80	160	ns	
$E_{on}$	$R_{Goff} = 6,8\ \Omega$	$T_j = 125\text{ }^\circ\text{C}$ $V_{GE} = -15\text{ V}$	16		mJ	
$t_{d(off)}$			400	520	ns	
$t_f$			70	100	ns	
$E_{off}$			12		mJ	
$R_{th(j-c)}$	per IGBT			0,15	K/W	

# SKM 145GB123D



**SEMITRANS® 2**

## IGBT Modules

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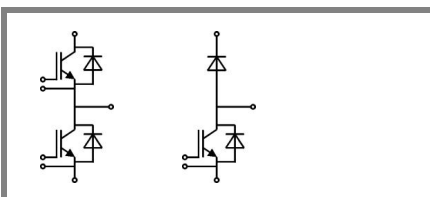
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- Low inductance case
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- High short circuit capability, self limiting to  $6 \times I_{cnom}$
- Latch-up free
- Fast & soft inverse CAL diodes
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### Typical Applications\*

- Switching (not for linear use)
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Characteristics					
Symbol	Conditions	min.	typ.	max.	Units
<b>Inverse Diode</b>					
$V_F = V_{EC}$	$I_{Fnom} = 100 \text{ A}; V_{GE} = 0 \text{ V}$	$T_j = 25 \text{ }^\circ\text{C}_{chiplev.}$	2	2,5	V
		$T_j = 125 \text{ }^\circ\text{C}_{chiplev.}$	1,8		V
$V_{F0}$		$T_j = 25 \text{ }^\circ\text{C}$	1,1	1,4	V
		$T_j = 125 \text{ }^\circ\text{C}$			V
$r_F$		$T_j = 25 \text{ }^\circ\text{C}$	9	11	mΩ
		$T_j = 125 \text{ }^\circ\text{C}$			mΩ
$I_{RRM}$	$I_F = 100 \text{ A}$	$T_j = 25 \text{ }^\circ\text{C}$	35		A
$Q_{rr}$	$di/dt = 1000 \text{ A}/\mu\text{s}$		5		μC
$E_{rr}$	$V_{GE} = 0 \text{ V}; V_{CC} = 600 \text{ V}$				mJ
$R_{th(j-c)D}$	per diode			0,36	K/W
<b>Freewheeling Diode</b>					
$V_F = V_{EC}$	$I_{Fnom} = 150 \text{ A}; V_{GE} = 0 \text{ V}$	$T_j = 25 \text{ }^\circ\text{C}_{chiplev.}$	2	2,5	V
		$T_j = 125 \text{ }^\circ\text{C}_{chiplev.}$	1,8		V
$V_{F0}$		$T_j = 25 \text{ }^\circ\text{C}$	1,1	1,4	V
		$T_j = 125 \text{ }^\circ\text{C}$			V
$r_F$		$T_j = 25 \text{ }^\circ\text{C}$	9	11	V
		$T_j = 125 \text{ }^\circ\text{C}$			V
$I_{RRM}$	$I_F = 150 \text{ A}$	$T_j = 25 \text{ }^\circ\text{C}$	55		A
$Q_{rr}$			8		μC
$E_{rr}$	$V_{GE} = 0 \text{ V}; V_{CC} = 600 \text{ V}$				mJ
$R_{th(j-c)FD}$	per diode			0,3	K/W
<b>Module</b>					
$L_{CE}$				30	nH
$R_{CC'+EE'}$	res., terminal-chip	$T_{case} = 25 \text{ }^\circ\text{C}$	0,75		mΩ
		$T_{case} = 125 \text{ }^\circ\text{C}$	1		mΩ
$R_{th(c-s)}$	per module			0,05	K/W
$M_s$	to heat sink M6		3	5	Nm
$M_t$	to terminals M5		2,5	5	Nm
w				160	g

This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

\* The specifications of our components may not be considered as an assurance of component characteristics. Components have to be tested for the respective application. Adjustments may be necessary. The use of SEMIKRON products in life support appliances and systems is subject to prior specification and written approval by SEMIKRON. We therefore strongly recommend prior consultation of our personal.

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## IGBT Modules

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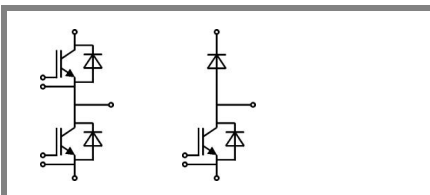
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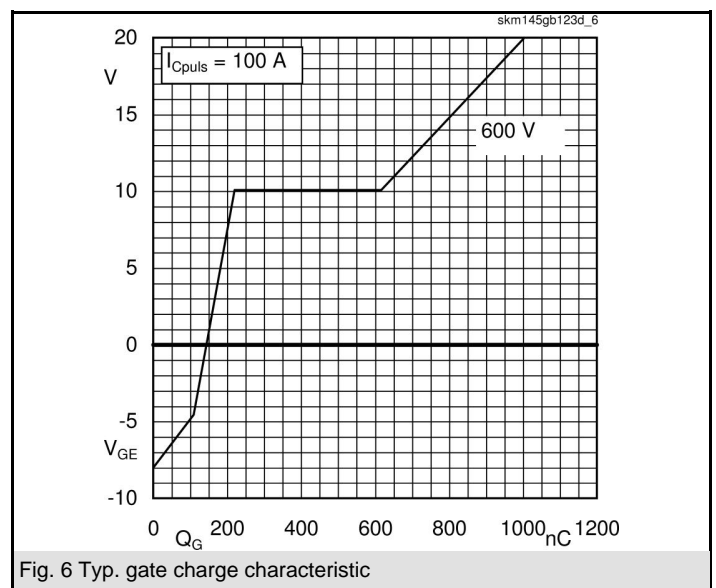
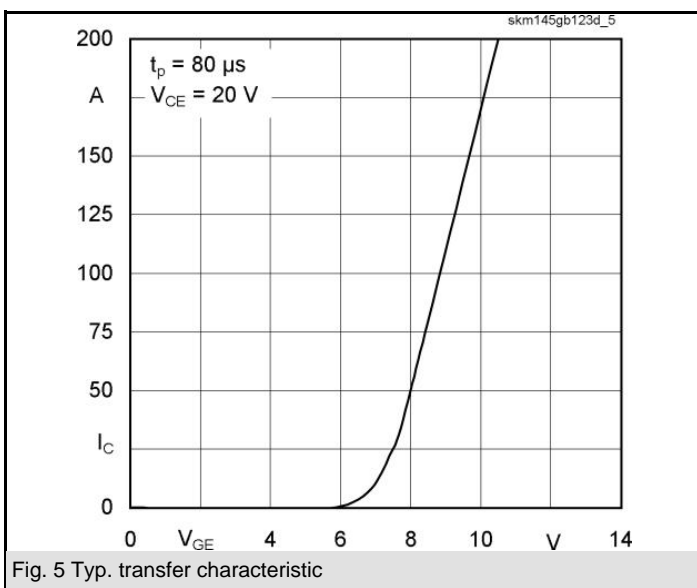
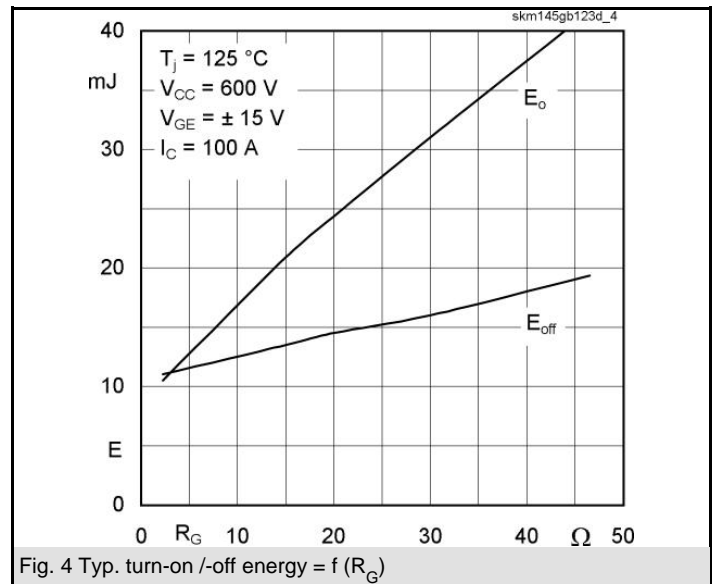
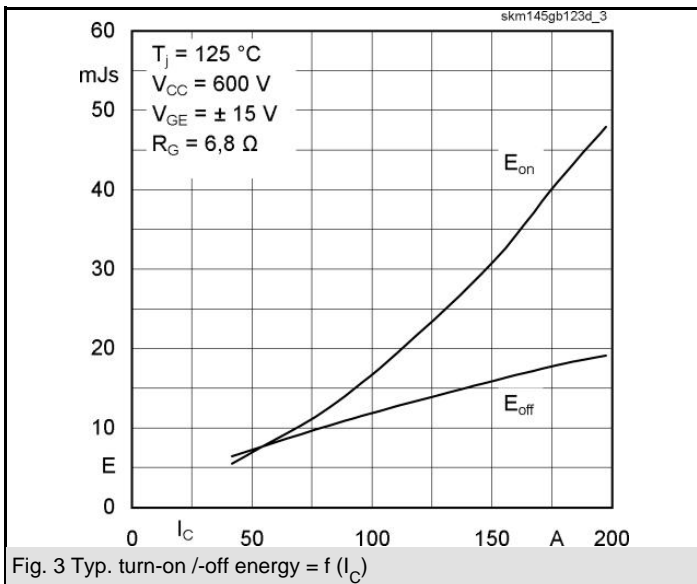
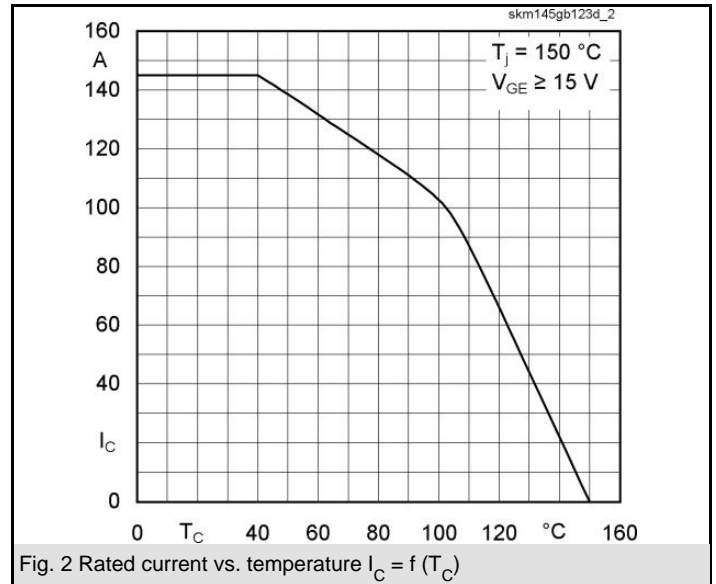
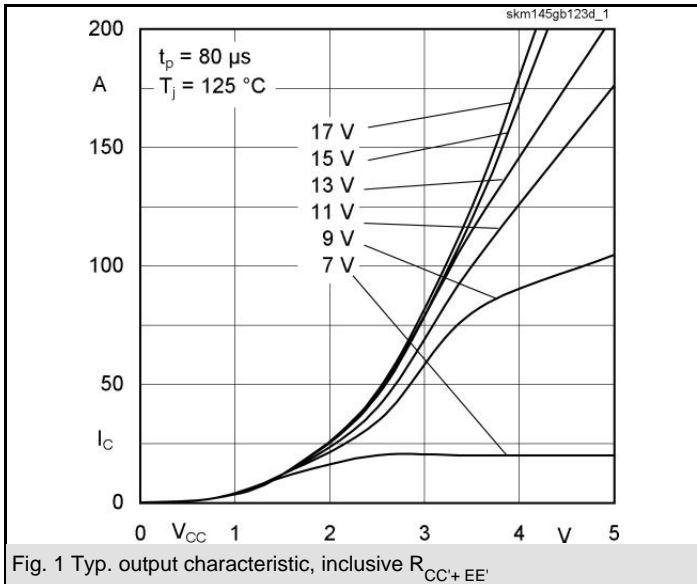
- Switching (not for linear use)
- AC inverter drives

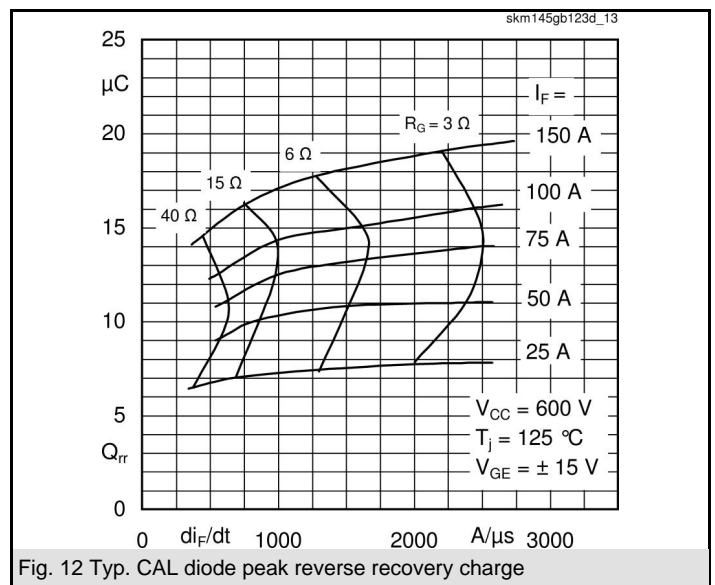
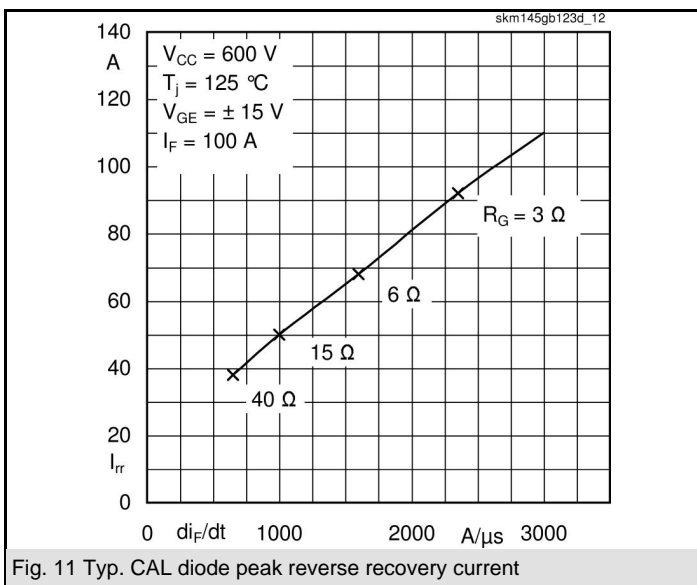
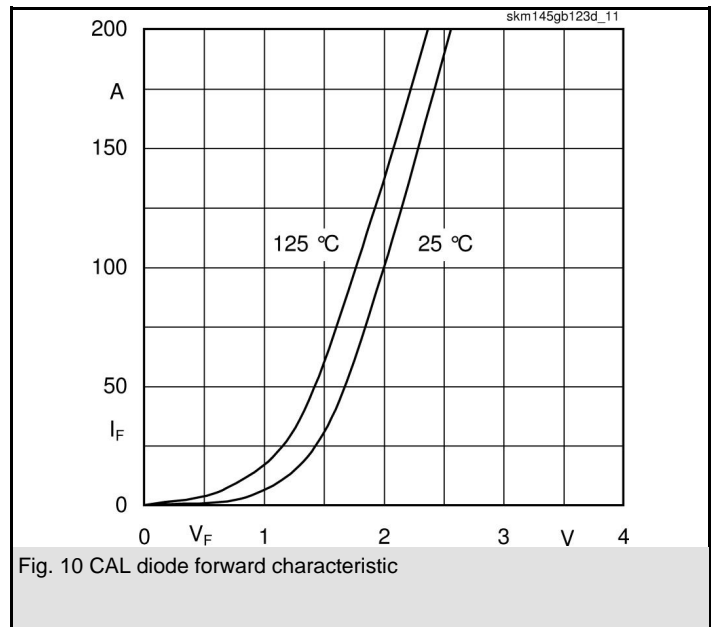
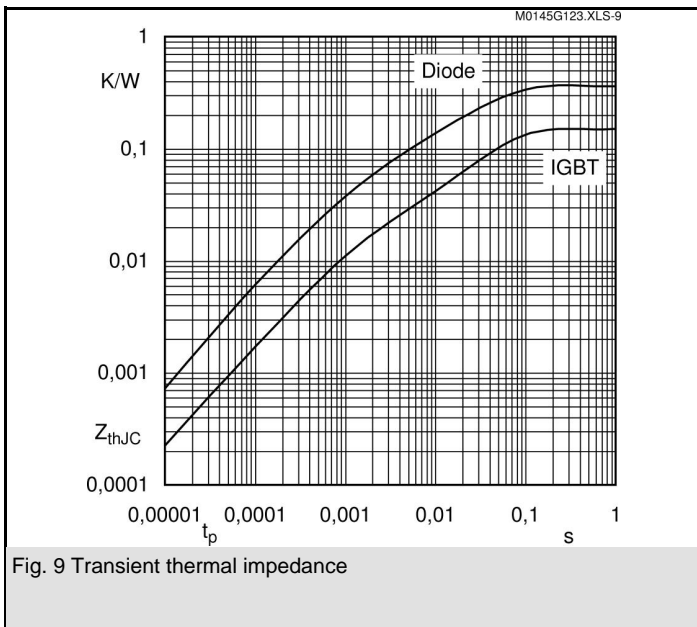
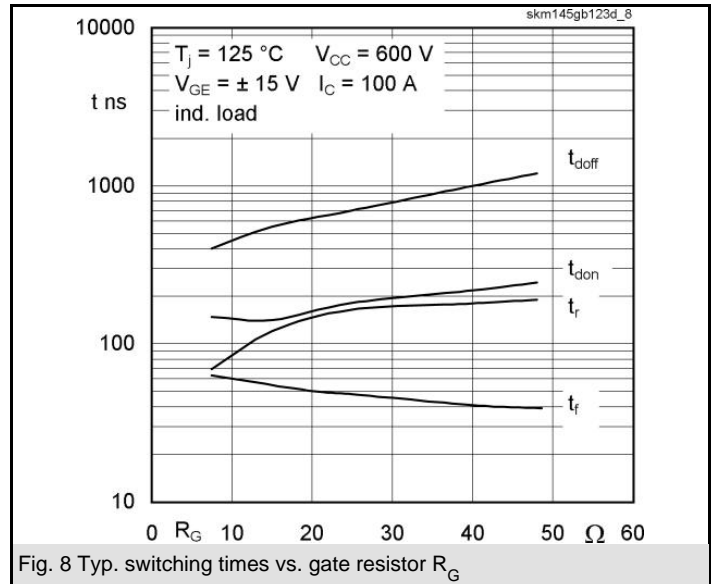
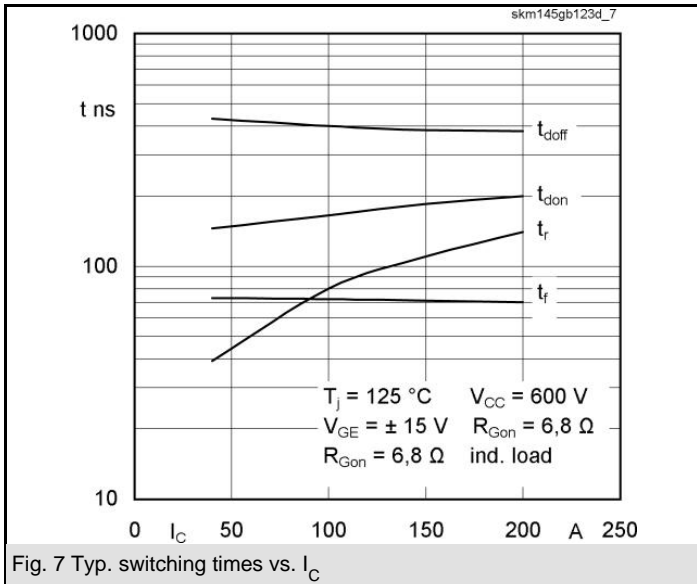
$Z_{th}$				
Symbol	Conditions	Values		Units
$Z_{th(j-c)I}$				
$R_{\theta j-c}$	$i = 1$	100		mk/W
$R_{\theta j-c}$	$i = 2$	38		mk/W
$R_{\theta j-c}$	$i = 3$	10		mk/W
$R_{\theta j-c}$	$i = 4$	2		mk/W
$\tau_{th j-c}$	$i = 1$	0,03		s
$\tau_{th j-c}$	$i = 2$	0,0287		s
$\tau_{th j-c}$	$i = 3$	0,0012		s
$\tau_{th j-c}$	$i = 4$	0,0002		s
$Z_{th(j-c)D}$				
$R_{\theta j-c}$	$i = 1$	240		mk/W
$R_{\theta j-c}$	$i = 2$	95		mk/W
$R_{\theta j-c}$	$i = 3$	22		mk/W
$R_{\theta j-c}$	$i = 4$	3		mk/W
$\tau_{th j-c}$	$i = 1$	0,054		s
$\tau_{th j-c}$	$i = 2$	0,0113		s
$\tau_{th j-c}$	$i = 3$	0,0012		s
$\tau_{th j-c}$	$i = 4$	0,005		s



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# SKM 145GB123D

UL Recognized

CASED61

File no. E 63 532



Case D 61



GB

Case D 61



GAL

Case D 62 (→ D 61)